

NP35N04YLG

R07DS0182EJ0100

Rev.1.00

Oct 22, 2010

MOS FIELD EFFECT TRANSISTOR

Description

The NP35N04YLG is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Low on-state resistance
 - $R_{DS(on)} = 9.7 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 17.5 \text{ A}$)
 - $R_{DS(on)} = 15 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 5 \text{ V}$, $I_D = 17.5 \text{ A}$)
- Logic level drive type
- Gate to Source ESD protection diode built in
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
NP35N04YLG -E1-AY ^{*1}	Pure Sn (Tin)	Tape 2500 p/reel	8-pin HSON, Taping (E1 type)
NP35N04YLG -E2-AY ^{*1}			8-pin HSON, Taping (E2 type)

Note: ^{*1}. Pb-free (This product does not contain Pb in the external electrode.)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DS}	40	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 35	A
Drain Current (pulse) ^{*1}	$I_{D(pulse)}$	± 105	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	77	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{*2}	P_{T2}	1.0	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Repetitive Avalanche Current ^{*3}	I_{AR}	22	A
Repetitive Avalanche Energy ^{*3}	E_{AR}	48	mJ

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.95	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance ^{*2}	$R_{th(ch-A)}$	150	$^\circ\text{C/W}$

Notes: ^{*1}. $T_C = 25^\circ\text{C}$, $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

^{*2}. Mounted on glass epoxy substrate of 40 mm x 40 mm x 0.8 mm

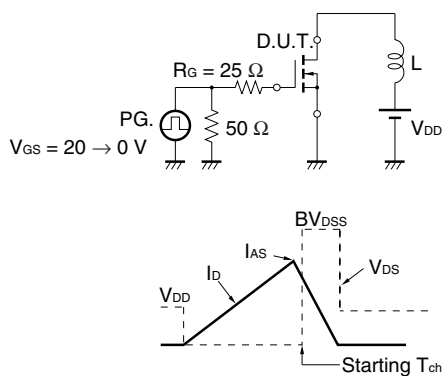
^{*3}. $T_{ch(peak)} \leq 150^\circ\text{C}$, $R_G = 25 \Omega$

Electrical Characteristics (T_A = 25°C)

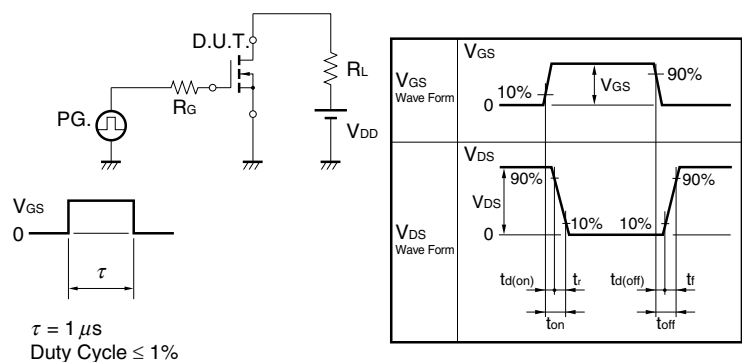
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 40 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	1.4	1.9	2.5	V	V _{DS} = V _{GS} , I _D = 250 μA
Forward Transfer Admittance *1	y _{fs}	15	30		S	V _{DS} = 5 V, I _D = 17.5 A
Drain to Source On-state Resistance *1	R _{DS(on)1}		7.8	9.7	mΩ	V _{GS} = 10 V, I _D = 17.5 A
Drain to Source On-state Resistance *1	R _{DS(on)2}		9.6	15	mΩ	V _{GS} = 5 V, I _D = 17.5 A
Input Capacitance	C _{iss}		1900	2850	pF	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz
Output Capacitance	C _{oss}		190	290	pF	
Reverse Transfer Capacitance	C _{rss}		120	220	pF	
Turn-on Delay Time	t _{d(on)}		13	26	ns	V _{DD} = 20 V, I _D = 17.5 A, V _{GS} = 10 V, R _G = 0 Ω
Rise Time	t _r		11	27	ns	
Turn-off Delay Time	t _{d(off)}		43	86	ns	
Fall Time	t _f		5	12	ns	V _{DD} = 32 V, V _{GS} = 10 V, I _D = 35 A
Total Gate Charge	Q _G		34	51	nC	
Gate to Source Charge	Q _{GS}		6		nC	
Gate to Drain Charge	Q _{GD}		10		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}		0.91	1.5	V	I _F = 35 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		27		ns	I _F = 35 A, V _{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q _{rr}		25		nC	

Note: *1. Pulsed

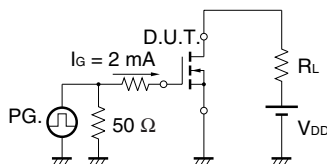
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

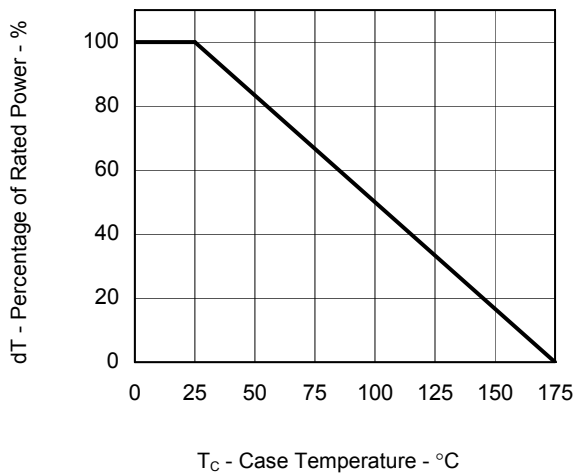


TEST CIRCUIT 3 GATE CHARGE

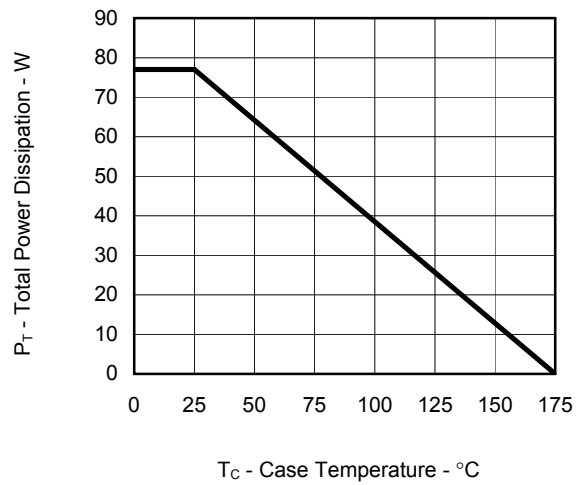


Typical Characteristics ($T_A = 25^\circ\text{C}$)

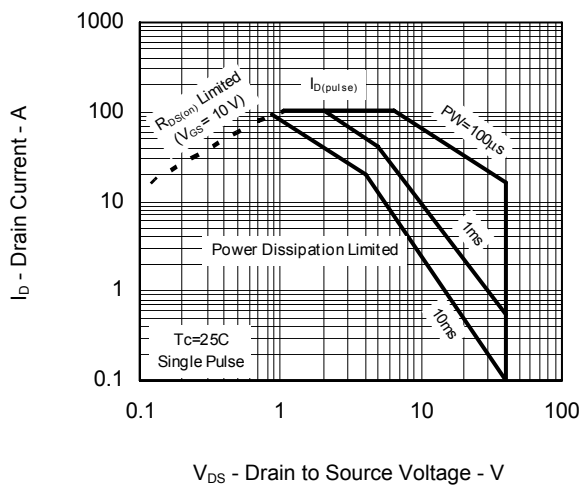
DERATING FACTOR OF FORWARD BIAS SAFE
OPERATING AREA



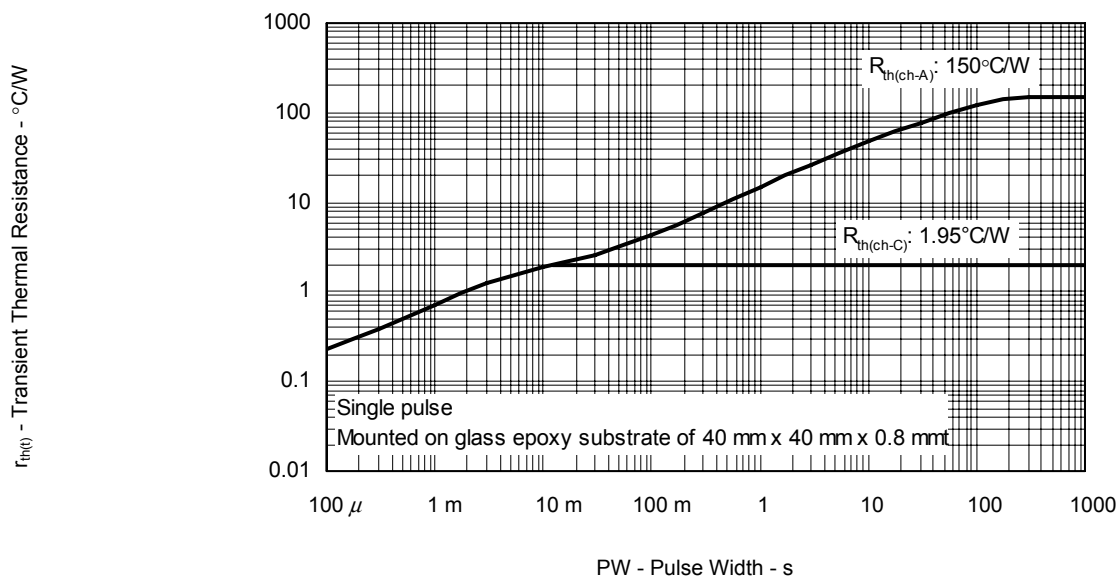
TOTAL POWER DISSIPATION vs.
CASE TEMPERATURE

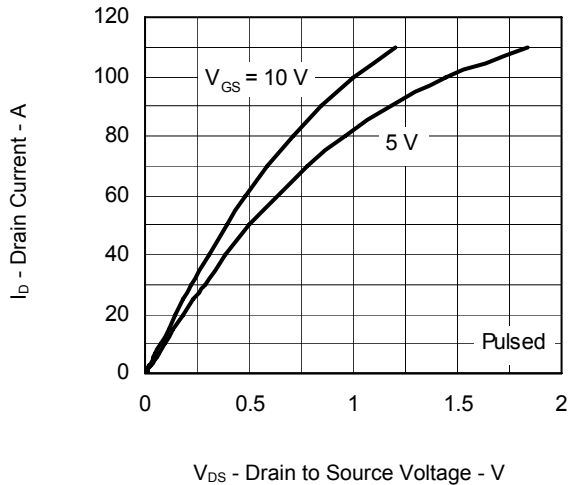


FORWARD BIAS SAFE OPERATING AREA

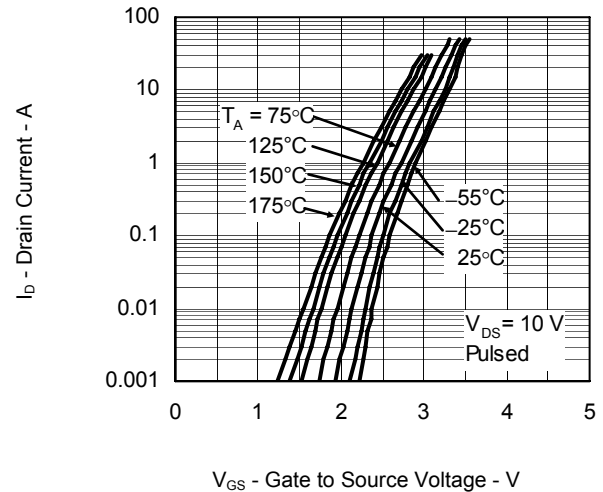
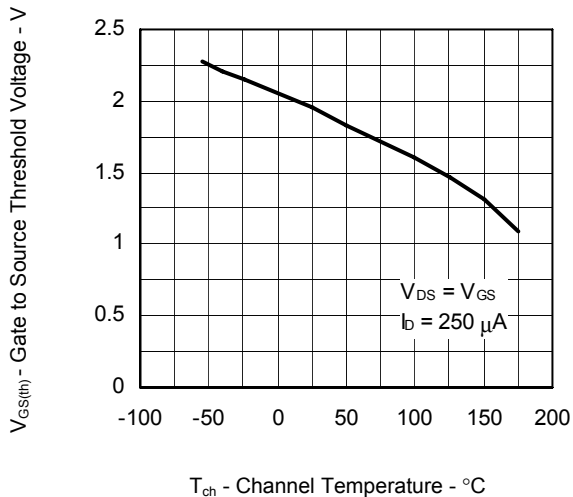
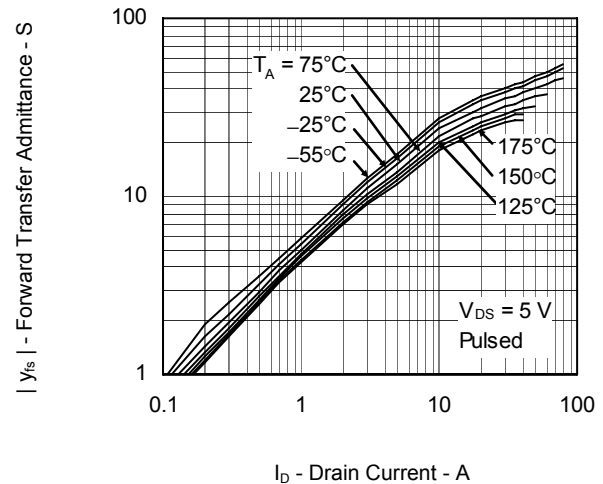
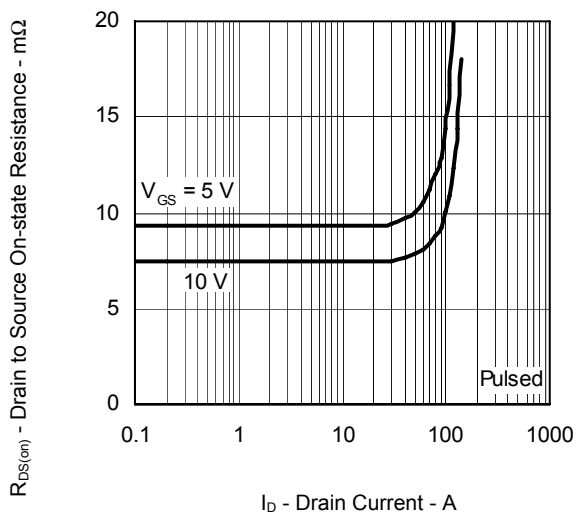
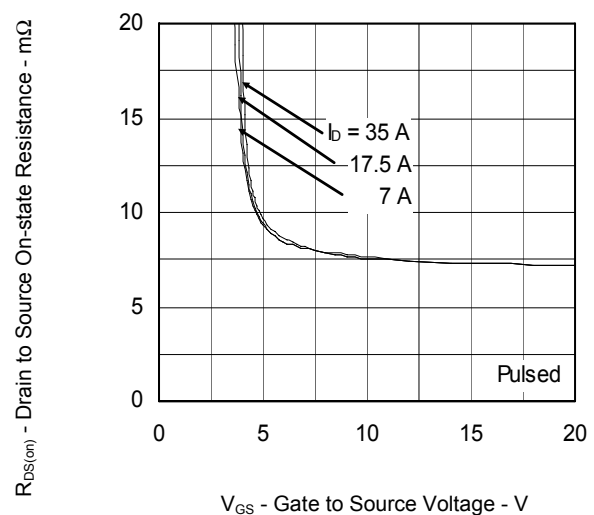


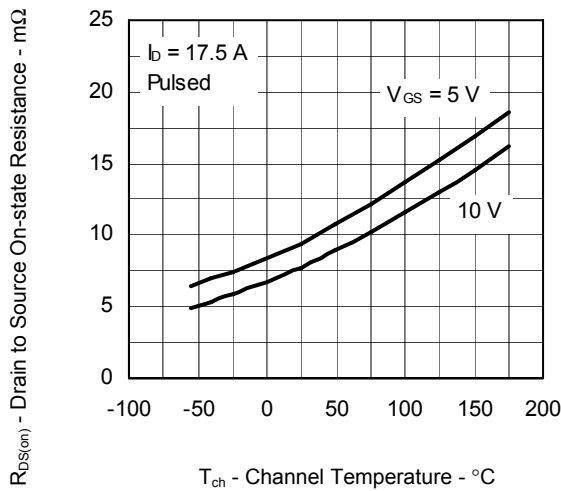
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



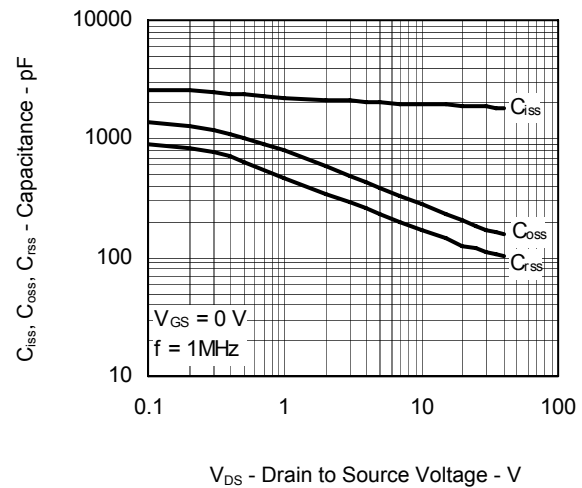
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

FORWARD TRANSFER CHARACTERISTICS

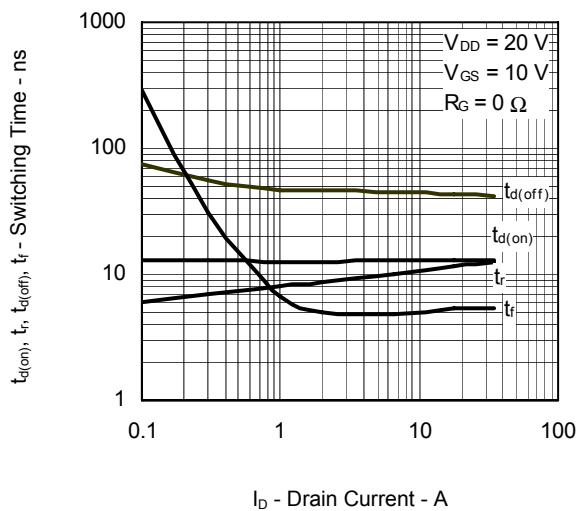
GATE TO SOURCE THRESHOLD VOLTAGE
vs. CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE vs. DRAIN
CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
CHANNEL TEMPERATURE

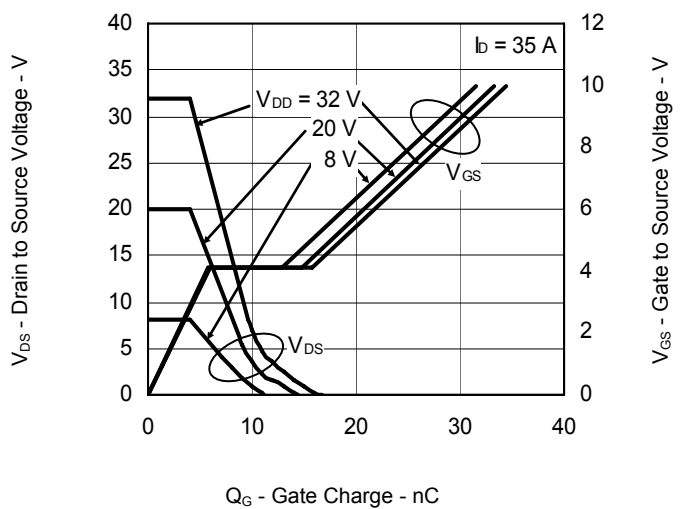
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



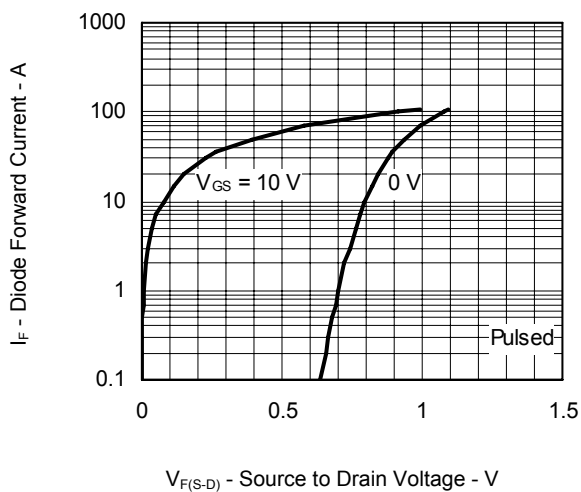
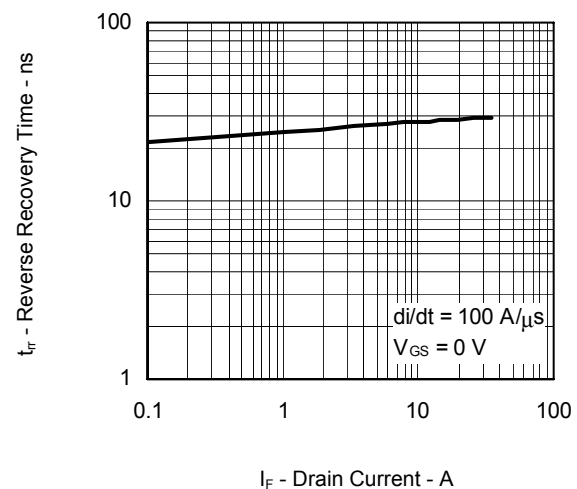
SWITCHING CHARACTERISTICS



DYNAMIC INPUT/OUTPUT CHARACTERISTICS

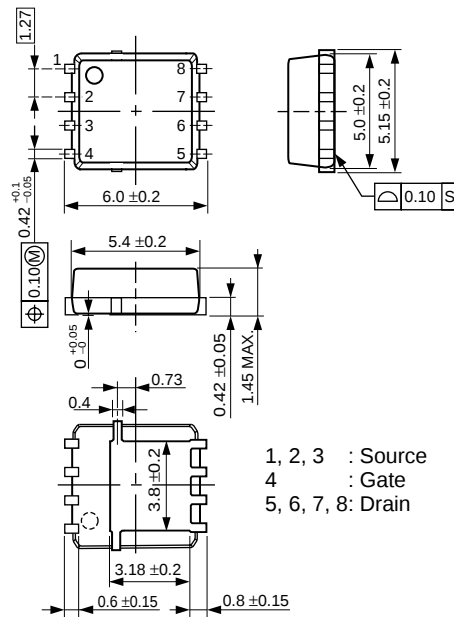


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

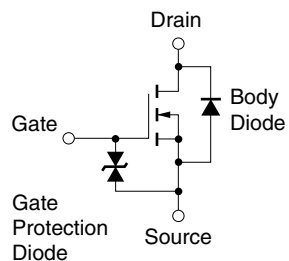
REVERSE RECOVERY TIME vs.
DRAIN CURRENT

Package Drawings (Unit: mm)

8-pin HSON (Mass: 0.13 g TYP.)



Equivalent Circuit



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Revision History	NP35N04YLG
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Rev.	Date	Description	
		Page	Summary
1.00	Oct 22, 2010	–	First Edition Issued

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